

MOS FIELD EFFECT TRANSISTOR

2SK2159

N-CHANNEL MOS FET FOR HIGH-SPEED SWITCHING

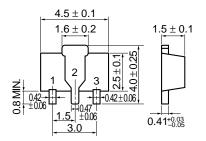
The 2SK2159 is an N-channel vertical type MOS FET featuring an operating voltage as low as 1.5 V. Because it can be driven on a low voltage and it is not necessary to consider driving current, the 2SK2159 is suitable for driving actuators of low-voltage portable systems such as headphone stereo sets and camcorders.

FEATURES

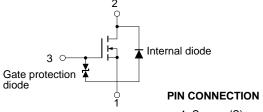
- · Capable of drive gate with 1.5 V
- Small RDS(on)

 $R_{DS(on)} = 0.7~\Omega~MAX.~~@V_{GS} = 1.5~V,~I_{D} = 0.1~A$ $R_{DS(on)} = 0.3~\Omega~MAX.~~@V_{GS} = 4.0~V,~I_{D} = 1.0~A$

PACKAGE DIMENSIONS (in millimeters)



EQUIVALENT CIRCUIT



1. Source (S)

2. Drain (D)

Marking: NW 3. Gate (G)

ABSOLUTE MAXIMUM RATINGS (TA = 25 °C)

PARAMETER	SYMBOL	TEST CONDITIONS	RATINGS	UNIT
Drain to Source Voltage	VDSS	Vgs = 0	60	V
Gate to Source Voltage	Vgss	V _{DS} = 0	±14	V
Drain Current (DC)	I _{D(DC)}		±2.0	Α
Drain Current (pulse)	ID(pulse)	PW ≤ 10 ms, Duty Cycle ≤ 50 %	±4.0	А
Total Power Dissipation	Рт	Mounted on 16 $\text{cm}^2 \times 0.7$ mm ceramic substrate.	2.0	W
Channel Temperature	Tch		150	°C
Storage Temperature	T _{stg}		-55 to +150	°C



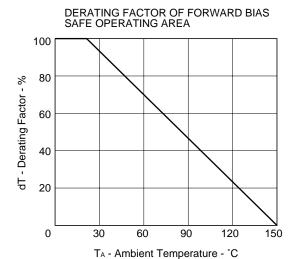
ELECTRICAL CHARACTERISTICS (TA = 25 °C)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Drain Cut-off Current	Ipss	V _{DS} = 60 V, V _{GS} = 0			1.0	μΑ
Gate Leakage Current	Igss	$V_{GS} = \pm 14 \text{ V}, V_{DS} = 0$			±10	μΑ
Gate Cut-off Voltage	Vgs(off)	V _{DS} = 10 V, I _D = 1 mA	0.5	0.9	1.1	V
Forward Transfer Admittance	yfs	V _{DS} = 10 V, I _D = 1.0 A	0.4			S
Drain to Source On-state Resistance	RDS(on)1	Vgs = 1.5 V, ID = 0.1 A		0.55	0.7	Ω
Drain to Source On-state Resistance	RDS(on)2	Vgs = 2.5 V, Ip = 1.0 A		0.27	0.5	Ω
Drain to Source On-state Resistance	RDS(on)3	Vgs = 4.0 V, ID = 1.0 A		0.22	0.3	Ω
Input Capacitance	Ciss	V _{DS} = 10 V, V _{GS} = 0,		319		pF
Output Capacitance	Coss	f = 1.0 MHz		109		pF
Reverse Transfer Capacitance	Crss			22		pF
Turn-On Delay Time	td(on)	V _{DD} = 25 V, I _D = 1.0 A		38		ns
Rise Time	tr	$V_{GS(on)} = 3 \text{ V}, \text{ Rg} = 10 \Omega$		128		ns
Turn-Off Delay Time	t _{d(off)}	$R_L = 25 \Omega$		237		ns
Fall Time	t _f			130		ns

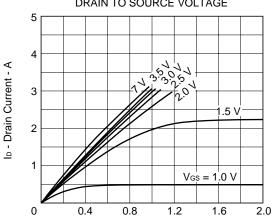
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TYPICAL CHARACTERISTICS (TA = 25 °C)

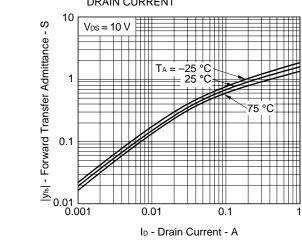




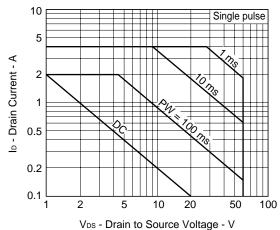


FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

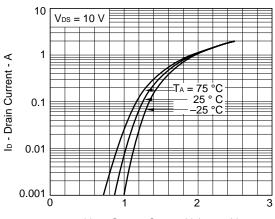
VDS - Drain to Source Voltage - V



FORWARD BIAS SAFE OPERATING AREA

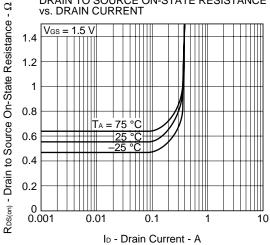


TRANSFER CHARACTERISTICS

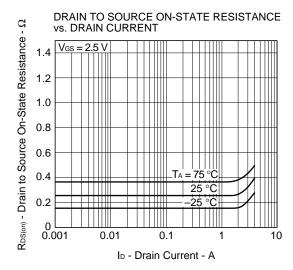


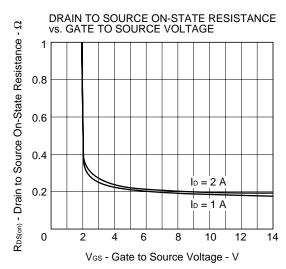
V_{GS} - Gate to Source Voltage - V

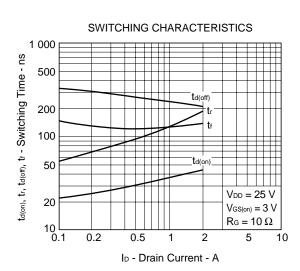
DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

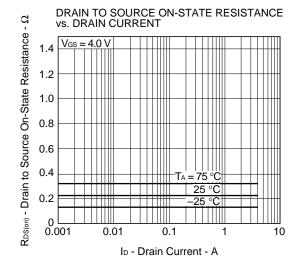


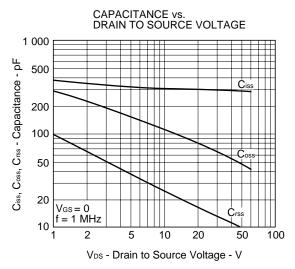


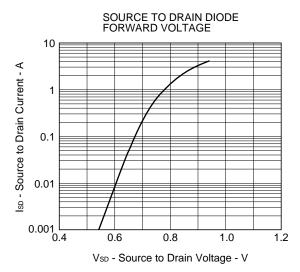














REFERENCE

Document Name	Document No.		
NEC semiconductor device reliability/quality control system	TEI-1202		
Quality grade on NEC semiconductor devices	IEI-1209		
Semiconductor device mounting technology manual	C10535E		
Guide to quality assurance for semiconductor devices	MEI-1202		
Semiconductor selection guide	X10679E		

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Anti-radioactive design is not implemented in this product.